

XPT IGBT

$$V_{CES} = 1200 \text{ V}$$

$$I_{C25} = 43 \text{ A}$$

$$V_{CE(sat)} = 1.8 \text{ V}$$

ISOPLUS™ Surface Mount Power Device

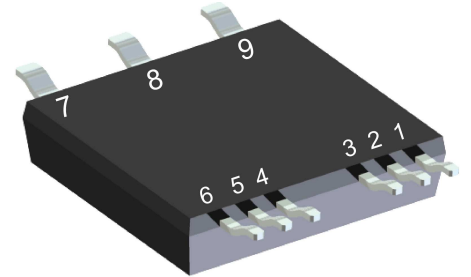
Boost Topology

Boost/Brake Chopper + free wheeling diode + Vcesat-Diode


Part number

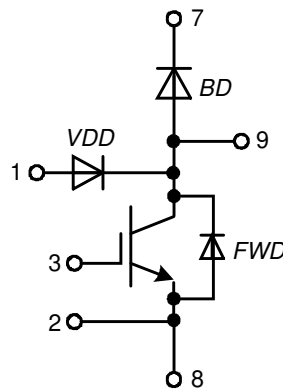
IXA30RG1200DHGLB

Marking on Product: IXA30RG1200DHGLB



Backside: isolated

 E72873



Features / Advantages:

- XPT IGBT
 - low saturation voltage
 - positive temperature coefficient for easy paralleling
 - fast switching
 - short tail current for optimized performance in resonant circuits
- Sonic™ diode
 - fast reverse recovery
 - low operating forward voltage
 - low leakage current
 - low temperature dependency of reverse recovery
- Vcesat detection diode (VDD)
 - integrated into package
 - very fast diode

Applications:

- AC drives
 - brake chopper
- PFC
 - boost chopper
- Switched reluctance drives

Package: SMPD

- Isolation Voltage: 3000 V~
- Industry convenient outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

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Free Wheeling Diode FWD

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			1200	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			1200	V
I_R	reverse current, drain current * not applicable, see Ices at IGBT	$V_R = 1200 V$	$T_{VJ} = 25^{\circ}C$		30	μA
		$V_R = 1200 V$	$T_{VJ} = 125^{\circ}C$		0.5	mA
V_F	forward voltage drop	$I_F = 30 A$	$T_{VJ} = 25^{\circ}C$		2.20	V
		$I_F = 60 A$				V
		$I_F = 30 A$	$T_{VJ} = 125^{\circ}C$		2.20	V
		$I_F = 60 A$				V
I_{FAV}	average forward current	$T_C = 80^{\circ}C$ rectangular $d = 0.5$	$T_{VJ} = 150^{\circ}C$		25	A
V_{F0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}C$		1.26	V
r_F	slope resistance				28	m Ω
R_{thJC}	thermal resistance junction to case				1	K/W
R_{thCH}	thermal resistance case to heatsink			0.30		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		125	W
I_{FSM}	max. forward surge current	$t = 10 ms; (50 Hz), sine; V_R = 0 V$	$T_{VJ} = 45^{\circ}C$		200	A
C_J	junction capacitance	$V_R = 400 V f = 1 MHz$	$T_{VJ} = 25^{\circ}C$	13		pF

VCEsat Detection Diode VDD

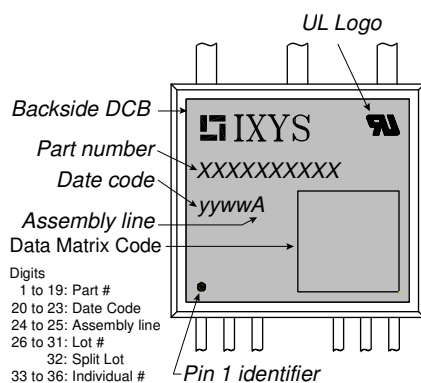
Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	Unit
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			1200	V
I_R	reverse current, drain current	$V_{R/D} = 1200 V$	$T_{VJ} = 25^{\circ}C$		2	μA
		$V_{R/D} = 1200 V$	$T_{VJ} = +02^{\circ}C$		0.03	mA
V_F	forward voltage drop	$I_F = 1 A$	$T_{VJ} = 25^{\circ}C$		2.20	V
		$I_F = 1 A$	$T_{VJ} = 12^{\circ}C$		1.80	V
V_{F0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}C$		1.30	V
r_F	slope resistance				390	m Ω
C_J	junction capacitance	$V_R = 400 V; f = 1 MHz$	$T_{VJ} = 25^{\circ}C$	tbd		pF
I_{RM}	max. reverse recovery current	} $V_R = +02 V; I_F = 1 A$ $-di/dt = +02 A/\mu s$	$T_{VJ} = 25^{\circ}C$		2.3	A
			$T_{VJ} = 125^{\circ}C$		tbd	A
t_{rr}	reverse recovery time		$T_{VJ} = 25^{\circ}C$		40	ns
			$T_{VJ} = 125^{\circ}C$		tbd	ns



Boost IGBT				Ratings					
Symbol	Definition	Conditions	min.	typ.	max.	Unit			
V_{CES}	collector emitter voltage	$T_{VJ} = 25^{\circ}\text{C}$			1200	V			
V_{GES}	max. DC gate voltage				± 20	V			
V_{GEM}	max. transient gate emitter voltage				± 30	V			
I_{C25}	collector current	$T_C = 25^{\circ}\text{C}$			43	A			
I_{C80}		$T_C = 80^{\circ}\text{C}$			30	A			
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$			147	W			
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 25\text{A}; V_{GE} = 15\text{V}$			1.8	V			
					2.1	V			
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 1\text{mA}; V_{GE} = V_{CE}$	5.4	5.9	6.5	V			
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{V}$			0.1	mA			
					0.1	mA			
I_{GES}	gate emitter leakage current	$V_{GE} = \pm 20\text{V}$			500	nA			
$Q_{G(on)}$	total gate charge	$V_{CE} = 600\text{V}; V_{GE} = 15\text{V}; I_C = 25\text{A}$		76		nC			
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 600\text{V}; I_C = 25\text{A}$ $V_{GE} = \pm 15\text{V}; R_G = 39\ \Omega$							
t_r	current rise time						$T_{VJ} = 125^{\circ}\text{C}$	70	ns
$t_{d(off)}$	turn-off delay time						40	ns	
t_f	current fall time						250	ns	
E_{on}	turn-on energy per pulse						100	mJ	
E_{off}	turn-off energy per pulse						3	mJ	
RBSOA	reverse bias safe operating area	$V_{GE} = \pm 15\text{V}; R_G = 39\ \Omega$							
I_{CM}		$V_{CEmax} = 1200\text{V}$			75	A			
SCSOA	short circuit safe operating area	$V_{CEmax} = 1200\text{V}$							
t_{SC}	short circuit duration	$V_{CE} = 900\text{V}; V_{GE} = \pm 15\text{V}$			10	μs			
I_{SC}	short circuit current	$R_G = 39\ \Omega$; non-repetitive		100		A			
R_{thJC}	thermal resistance junction to case				0.85	K/W			
R_{thCH}	thermal resistance case to heatsink				0.25	K/W			
Boost Diode BD									
V_{RRM}	max. repetitive reverse voltage	$T_{VJ} = 25^{\circ}\text{C}$			1200	V			
I_{F25}	forward current	$T_C = 25^{\circ}\text{C}$			48	A			
I_{F80}		$T_C = 80^{\circ}\text{C}$			32	A			
V_F	forward voltage	$I_F = 30\text{A}$			2.20	V			
					1.90	V			
I_R	reverse current	$V_R = V_{RRM}$			0.03	mA			
					0.15	mA			
Q_{rr}	reverse recovery charge	$V_R = 600\text{V}$ $-di_F/dt = 600\text{A}/\mu\text{s}$ $I_F = 30\text{A}; V_{GE} = 0\text{V}$							
I_{RM}	max. reverse recovery current						$T_{VJ} = 125^{\circ}\text{C}$	3.5	μC
t_{rr}	reverse recovery time						30	A	
E_{rec}	reverse recovery energy						350	ns	
R_{thJC}	thermal resistance junction to case				1	K/W			
R_{thCH}	thermal resistance case to heatsink				0.3	K/W			



Package SMPD		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			100	A
T_{VJ}	virtual junction temperature		-55		150	°C
T_{op}	operation temperature		-55		125	°C
T_{stg}	storage temperature		-55		150	°C
Weight				8.5		g
F_C	mounting force with clip		40		130	N
$d_{Spp/ App}$	creepage distance on surface / striking distance through air	terminal to terminal	1.6			mm
$d_{Spb/ Apb}$		terminal to backside	4.0			mm
V_{ISOL}	isolation voltage	t = 1 second	3000			V
		t = 1 minute	2500			V



Part description

- I = IGBT
- X = XPT IGBT
- A = Gen 1 / std
- 30 = Current Rating [A]
- RG = Boost/Brake Chopper + free wheeling diode + Vcesat-Diode
- 1200 = Reverse Voltage [V]
- D = Diode
- H = Sonic Fast Recovery Diode
- G = extreme fast
- LB = SMPD-B

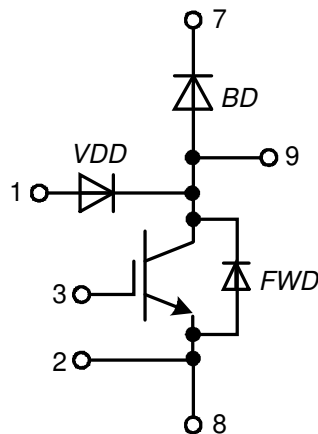
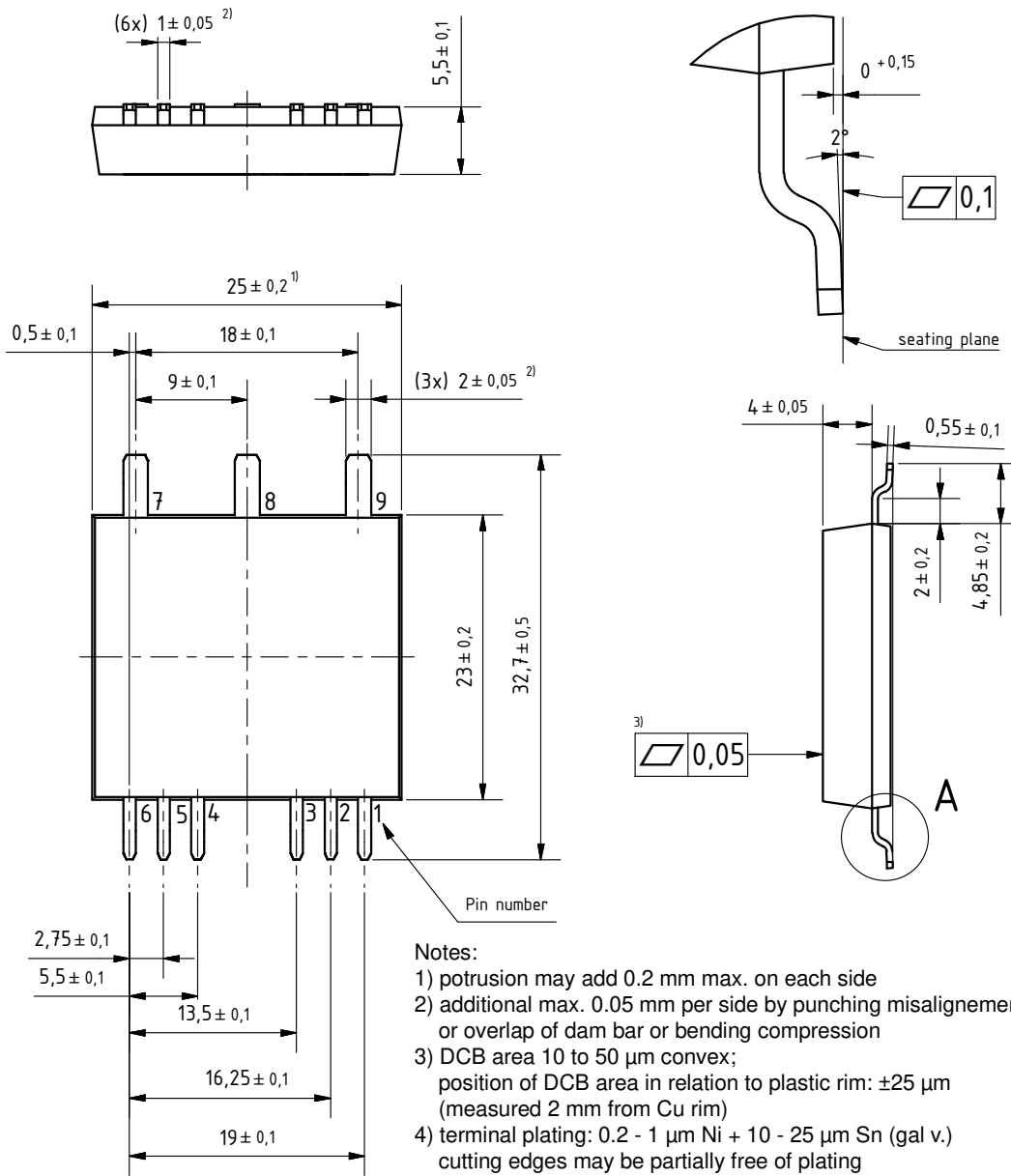
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	IXA30RG1200DHGLB-TUB	IXA30RG1200DHGLB	Tube	20	524072
Alternative	IXA30RG1200DHGLB-TRR	IXA30RG1200DHGLB	Tape & Reel	200	524079

Similar Part	Package	Voltage class
IXA20RG1200DHGLB	SMPD-B	1200
IXA40RG1200DHGLB	SMPD-B	1200



Outlines SMPD

A (8 : 1)





Boost IGBT

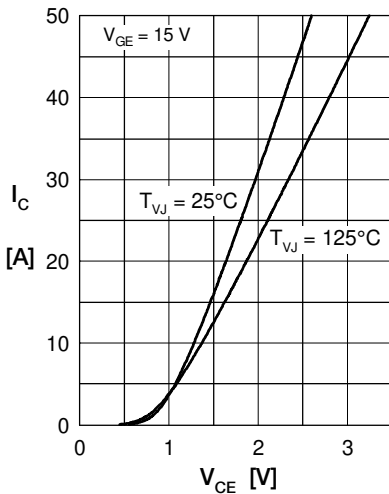


Fig. 1 Typ. output characteristics

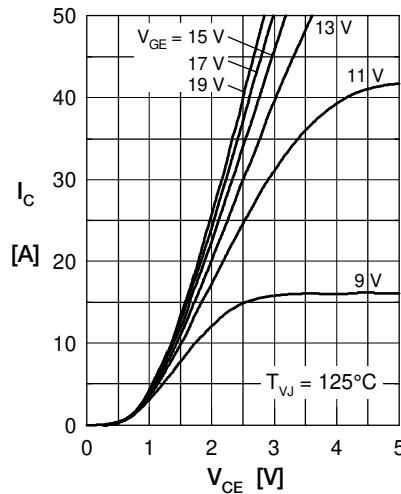


Fig. 2 Typ. output characteristics

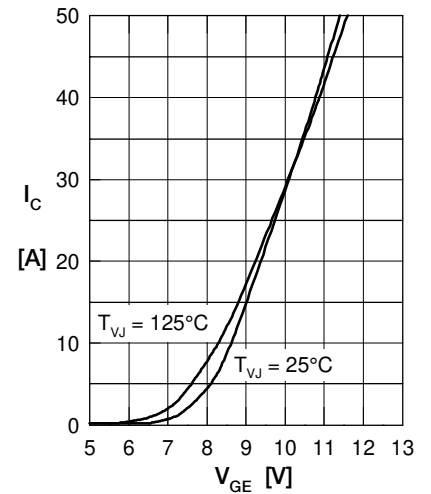


Fig. 3 Typ. transfer characteristics

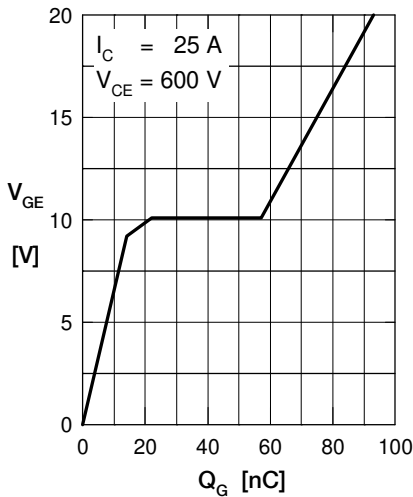


Fig. 4 Typ. turn-on gate charge

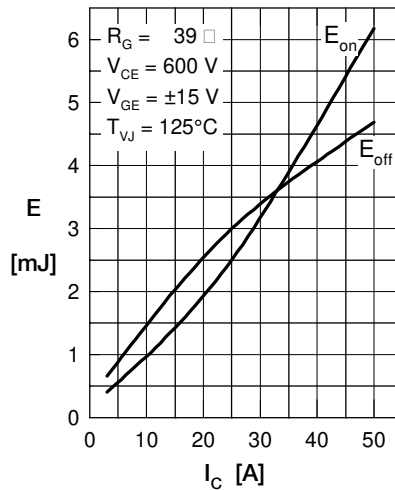


Fig. 5 Typ. switching energy versus collector current

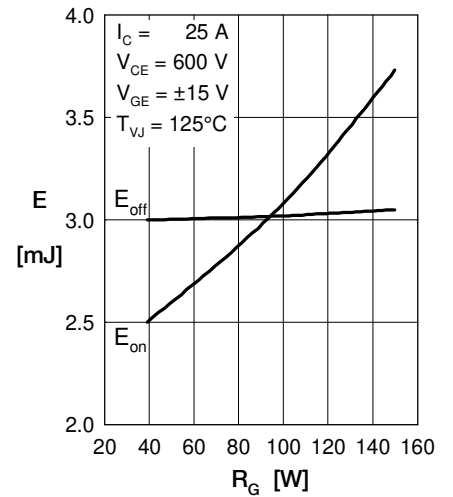


Fig. 6 Typ. switching energy versus gate resistance

Fig. 7 Typ. transient thermal impedance junction to case



Boost Diode BD

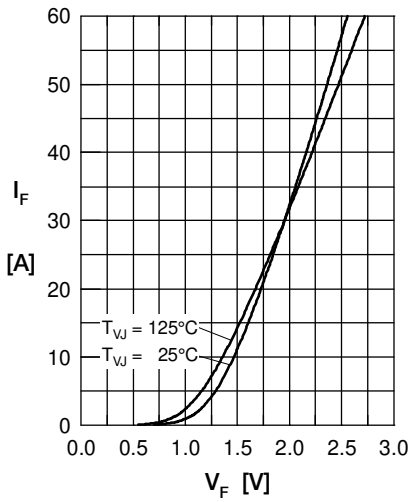


Fig. 1 Typ. Forward current versus V_F

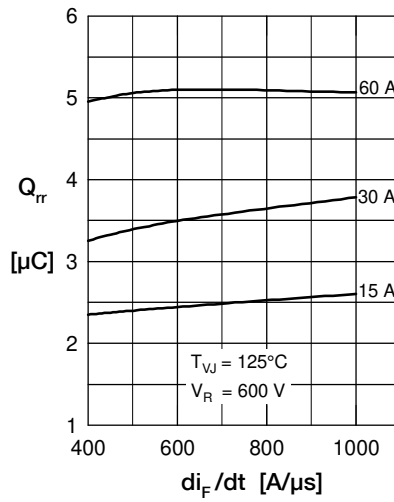


Fig. 2 Typ. reverse recov.charge Q_{rr} versus di/dt

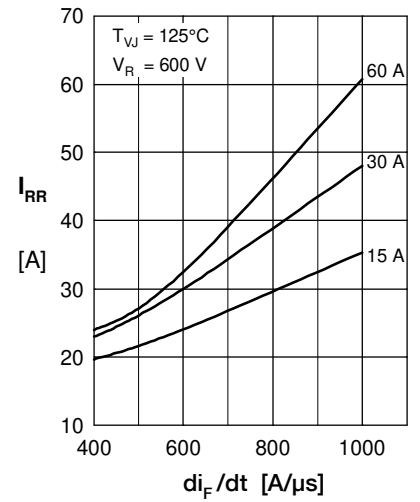


Fig. 3 Typ. peak reverse current I_{RM} versus di/dt

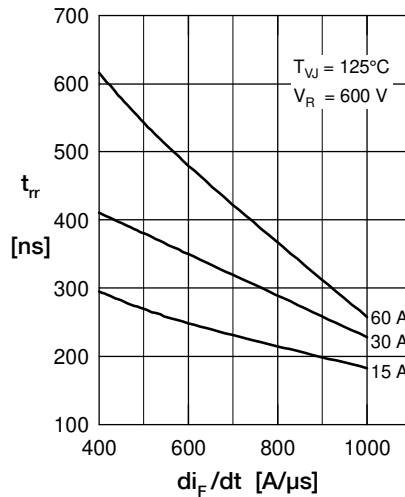


Fig. 4 Dynamic parameters Q_{rr} , I_{RM} versus di/dt

Fig. 5 Typ. recovery time t_{rr} versus di/dt

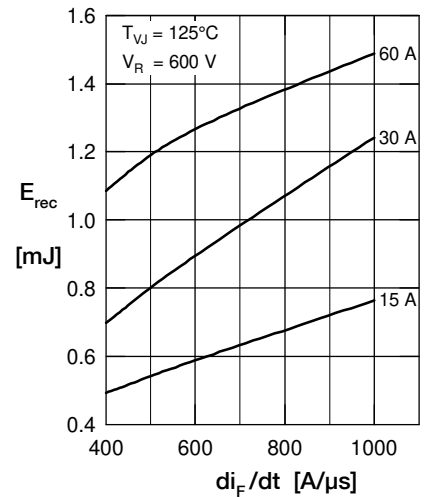


Fig. 6 Typ. recovery energy E_{rec} versus di/dt

Fig. 7 Typ. transient thermal impedance junction to case